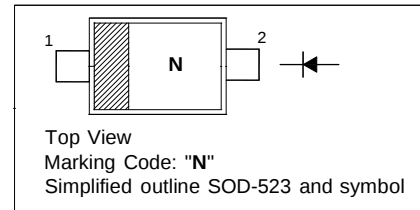


Silicon Epitaxial Schottky Barrier Diode

for high speed switching application

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	V_{RM}	15	V
Reverse Voltage	V_R	10	V
Average Forward Current	$I_{F(AV)}$	100	mA
Maximum (Peak) Forward Current	I_{FM}	200	mA
Surge Current (10 ms)	I_{FSM}	1	A
Power Dissipation	P_{tot}	150	mW
Operating Temperature Range	T_{opr}	- 40 to + 100	$^{\circ}\text{C}$
Junction Temperature	T_j	125	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 5\text{ mA}$ at $I_F = 100\text{ mA}$	V_F	0.3 0.5	V
Reverse Current at $V_R = 10\text{ V}$	I_R	20	μA
Total Capacitance at $V_R = 0$, $f = 1\text{ MHz}$	C_T	40	pF

